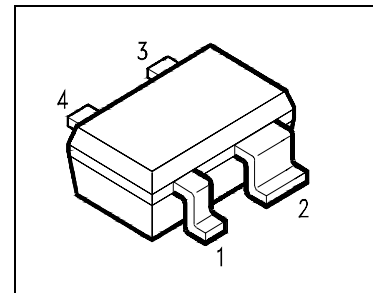


NPN Silicon-Germanium RF Transistor

Preliminary Data

- For high gain low noise amplifier
- Noise Figure $F = 0.65$ dB at 1.8 GHz
- $G_{ms} = 21$ dB at 1.8 GHz
- Gold metalization for high reliability
- 70GHz f_T - Line
- 10dBm Input IP_3 capability @ 1.95 GHz, $V_{CE} = 2V$, $I_{CE} = 6mA$



ESD: Electrostatic discharge sensitive device,
observe handling precautions!

| Type | Marking | Ordering Code (8-mm taped) | Pin Configuration | | | | Package |
|--------|---------|-------------------------------|-------------------|---|---|---|---------|
| | | | 1 | 2 | 3 | 4 | |
| BFP620 | | | B | E | C | E | SOT-343 |

Maximum Ratings

| Parameter | Symbol | | Unit |
|---|-----------|--------------|------|
| Collector-emitter voltage | V_{CEO} | 2.5 | V |
| Collector-base voltage | V_{CBO} | tbd | V |
| Emitter-base voltage | V_{EBO} | 1.5 | V |
| Collector current | I_C | 80 | mA |
| Base current | I_B | tbd | mA |
| Total power dissipation, $T_S \leq tbd.$ 1)2) | P_{tot} | tbd | mW |
| Junction temperature | T_j | tbd | °C |
| Ambient temperature range | T_A | -65...+150°C | °C |
| Storage temperature range | T_{stg} | -65...+150°C | °C |

Thermal Resistance

| | | | |
|-----------------------------|-------------|-----|-----|
| Junction-soldering point 1) | $R_{th JS}$ | tbd | K/W |
|-----------------------------|-------------|-----|-----|

1) T_S is measured on the emitter lead at the soldering point to the pcb.

2) P_{tot} due to Maximum Ratings.

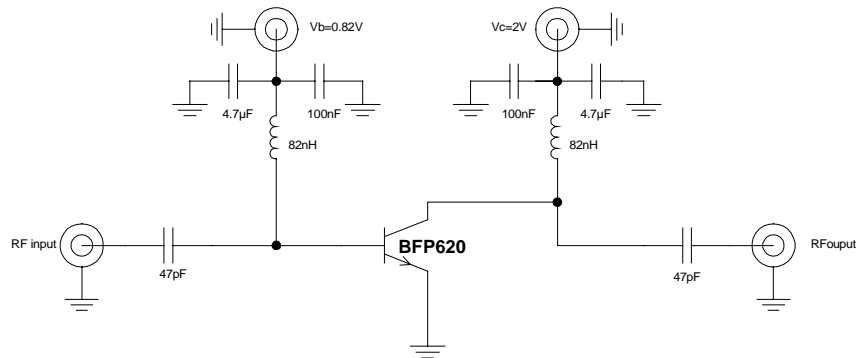
Electrical Characteristics

at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

| Parameter | Symbol | Value | | | Unit |
|---|---------------|-------|------|------|---------------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Collector-emitter breakdown voltage $I_C = 1\text{ mA}$ | $V_{(BR)CEO}$ | 2.5 | 2.8 | | V |
| Collector-cutoff current $V_{CB} = 5\text{ V}$, $I_E = 0\text{ mA}$ | I_{CBO} | - | - | 200 | nA |
| Emitter base cutoff current $V_{EB} = 1.5\text{ V}$, $I_C = 0\text{ mA}$ | I_{EBO} | - | - | 10 | μA |
| DC current gain $I_C = 20\text{ mA}$, $V_{CE} = 1.5\text{ V}$ | h_{FE} | 150 | 180 | 210 | |
| AC Characteristics | | | | | |
| Collector-base capacitance $V_{CB} = 2\text{ V}$, $V_{BE} = v_{be} = 0\text{ V}$, $f = 1\text{ MHz}$ | C_{cb} | - | 0.11 | 0.2 | pF |
| Collector-emitter capacitance $V_{CE} = 2\text{ V}$, $V_{BE} = v_{be} = 0\text{ V}$, $f = 1\text{ MHz}$ | C_{ce} | - | 0.18 | - | pF |
| Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $V_{CB} = v_{cb} = 0\text{ V}$, $f = 1\text{ MHz}$ | C_{eb} | - | 0.45 | - | pF |
| Noise figure $I_C = 3\text{ mA}$, $V_{CE} = 1.5\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$ | F | - | 0.65 | | dB |
| Power gain $I_C = 20\text{ mA}$, $V_{CE} = 1.5\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$ | $G_{ms}^{1)}$ | - | 21 | - | dB |
| Insertion power gain $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\Omega$ | $ S_{21} ^2$ | | 19 | - | dB |
| Third order intercept point at output $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$ | OIP_3 | - | 22 | - | dBm |
| 1dB Compression point $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$ | P_{-1dB} | - | 12 | - | dBm |

$$1) G_{ms} = \left| \frac{S_{21}}{S_{12}} \right|$$

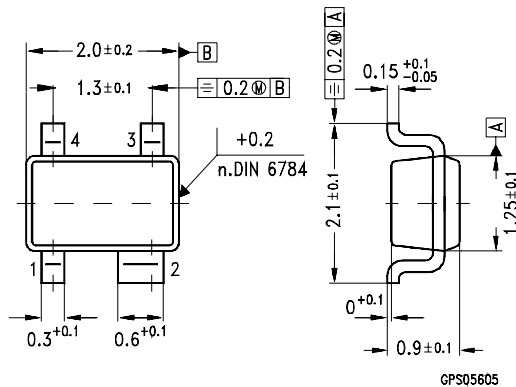
Test Circuit For High IIP₃



| SYMBOL | PARAMETER | MIN | TYP | MAX | UNIT |
|--------------|-----------------------------|-----|------|-----|------|
| $ S_{21} ^2$ | Insertion Power Gain | tbd | 16.5 | - | dB |
| NF | Noise figure (50Ω) | - | 1.1 | tbd | dB |
| IIP3 | Input Third Order Intercept | tbd | 10 | - | dBm |
| RLout | Output Return Loss | - | 10 | - | dB |
| RLin | Input Return Loss | - | 6 | - | dB |

Conditions: $f=1950\text{MHz}$, $I_{CE}=6\text{mA}$, $Z_L=Z_S=50\Omega$

Package



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